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Application Number	10/026,019
Filing Date	December 27, 2001
First Named Inventor	Ralph Johnson
Group Art Unit	2828
Examiner Name	Tuan M Nguyen
Attorney Docket Number	V637-02674 US

✓	SEKIGUCHI, S., et al., "Long wavelength GaInAsP/InP laser with n-n contacts using AlAs/InP hole injecting tunnel junction", article, Japanese Journal of Applied Physics, Part 2, No 4B, 04-15-1999, pgs L443-5.
✓	STARCK, C., "Long wavelength VCSEL with tunnel junction and metamorphic AlAs/GaAs conductive DBR", article, Physics Review B, Vol 39, No 3, 01-15-1989, pgs 1871-83.
✓	SUGIMOTO, M., et al., "Surface emitting devices with distributed Bragg reflectors grown by highly precise molecular beam epitaxy", article, Journal of Crystal Growth, Vol 127, 1995, pgs 1-4.
✓	UCHIDA, T., et al., "CBE grown 1.5 μm GaInAsP/InP surface emitting lasers", article, IEEE Journal of Quantum Electronics, Vol 29, No 6, Jun 1993, pgs 1975-80.
✓	VAN DE WALLE, C., "Band lineups and deformation potentials in the model-solid theory", article, Physical Review B, Vol 39, No 3, 01-15-1989, pgs 1871-83.
✓	WHITAKER, T., "Long wavelength VCSELs move closer to reality", article, Compound Semiconductor, July 2000, pgs 65-7.
✓	YAMADA, M., et al., "Low-threshold lasing at 1.3 μm from GaAsSb quantum wells directly grown on GaAs substrates", article, IEEE, 0-7803-4947, 04/1998, pgs 149-50.
✓	YAMADA, M., et al., "Room temperature low-threshold CW operation of 1.23 μm GaAsSb VCSELs on GaAs substrates", article, Electronics Letters, 03-30-2000, Vol 36, No 7, pgs 637-638.
✓	YANG, X., et al., "High performance 1.3 μm InGaAsN:Sb/GaAs quantum well lasers grown by molecular beam epitaxy", journal article, Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures, Vol. 18, No 3, Oct 1999, pgs 1484-7.
✓	YANG, X., et al., "InGaAsN/GaAs quantum wells for 1.55 μm lasers grown by molecular-beam epitaxy", article, Applied Physics Letters, Vol 78, No 26, pgs 4068-70.
✓	YANO, M., et al., "Time-resolved reflection high energy electron diffraction analysis for atomic layer depositions of GaSb by molecular beam epitaxy", article, Journal of Crystal Growth, Vol 146, 1995, pgs 349-53.
✓	YUEN, W., et al., "High-performance 1.5 μm single-epitaxy top-emitting VCSEL", article, Electronics Letters, Vol 36, No 13, 06-22-2000, pgs 1121-3.

Examiner  
SignatureDate  
Considered

02/04/04

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